



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
Applicant : Ohtani, et al. Art Unit : 2815  
Serial No.: 09/379,702 Examiner : Eugene Lee  
Filed : August 24, 1999  
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICES

**BOX AF**

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE

In response to the action mailed June 21, 2001, please  
amend the application as follows:

In the specification:

Please replace the paragraph beginning at page 16, line 4,  
with the following rewritten paragraph:

DI -- As shown in Fig. 2(C), dopant ions are implanted into  
the active layer 107 by ion implantation techniques, using the  
gate electrode 111 and surrounding anodic oxide 112 as a mask.  
In order to fabricate a N-channel TFT, phosphorus is introduced.  
Using phosphine (PH<sub>3</sub>) as a dopant gas, phosphorus ions are  
implanted. On the other hand, in order to fabricate a P-channel

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I hereby certify under 37 CFR §1.8(a) that this  
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TECHNICAL  
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10-2-01

T.F.H.  
1-12-02  
Payton